

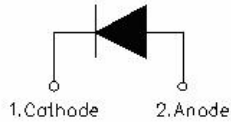
MBRF10150 SCHOTTKY RECTIFIER



Features

- 175°C T_J operation
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- This is a Pb – Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Circuit Diagram



Applications

- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection
- Center tap configuration

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	-	150	V
Average Rectified Forward Current	I _{F(AV)}	50% duty cycle @T _c =155°C, rectangular wave form	10	A
Peak One Cycle Non-Repetitive Surge Current	I _{FSM}	8.3ms, Half Sine pulse	138	A

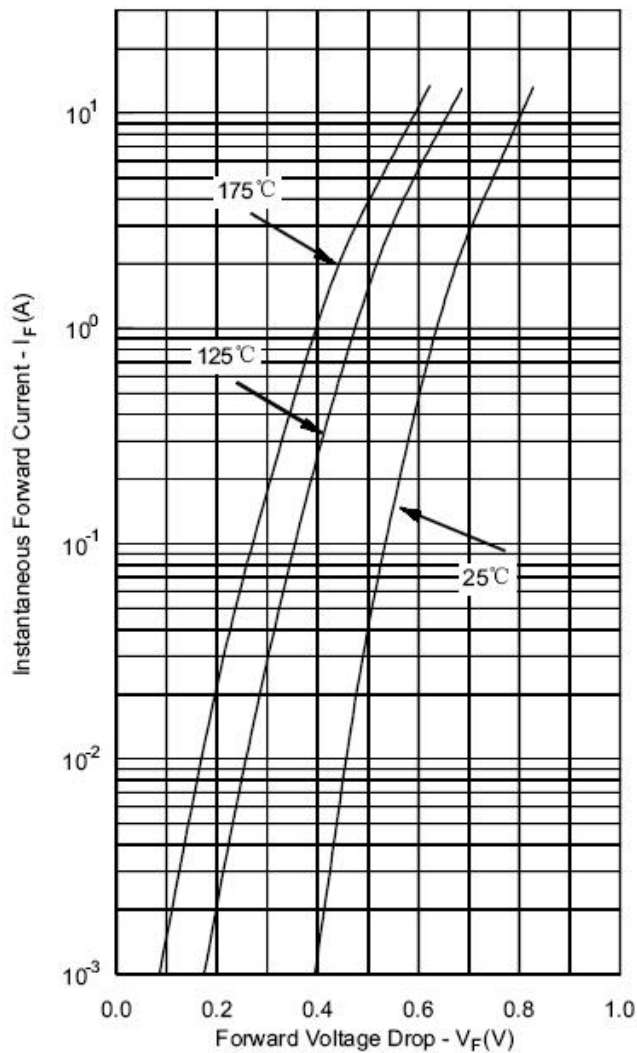
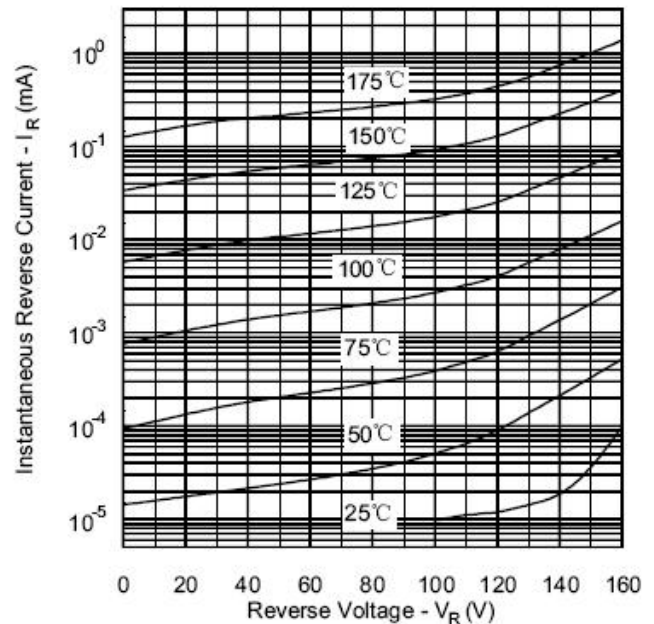
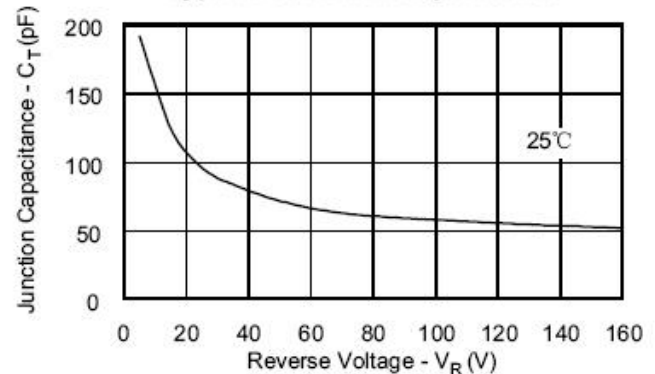
Electrical Characteristics:

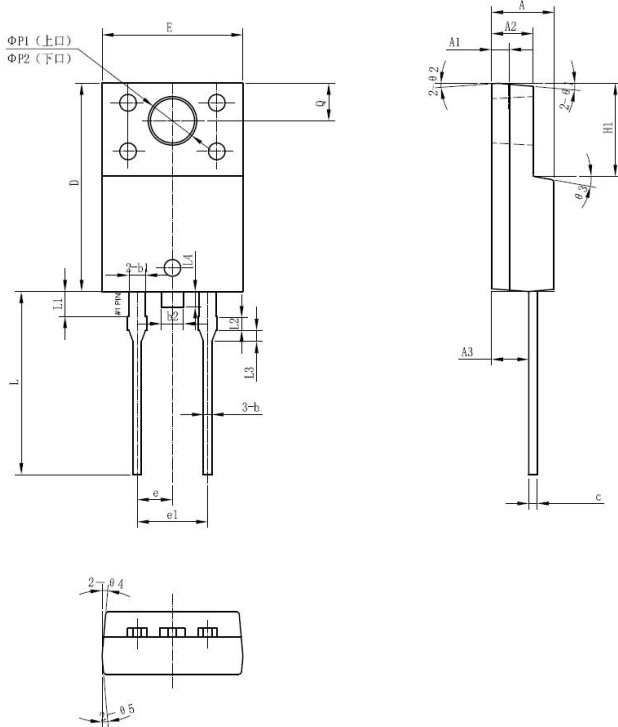
Characteristics	Symbol	Condition	Typ.	Max.	Units
Forward Voltage Drop*	V _{F1}	@ 10A, Pulse, T _J = 25 °C	0.80	1.10	V
	V _{F2}	@ 10A, Pulse, T _J = 125 °C	0.68	0.86	V
Reverse Current*	I _{R1}	@V _R = rated V _R , T _J = 25 °C	0.001	1.0	mA
	I _{R2}	@V _R = rated V _R , T _J = 125 °C	0.1	7.0	mA
Non-Repetitive Avalanche Energy	E _{AS}	T _J = 25 °C, I _{AS} = 2 A, L = 1mH	-	2	mJ
Junction Capacitance	C _T	@V _R = 5V, T _C = 25 °C f _{SIG} = 1MHz	180	400	pF
Series Inductance	L _S	Measured lead to lead 5 mm from package body	8	-	nH
Voltage Rate of Change	dv/dt	-	-	10,000	V/μs

* Pulse width < 300 μs, duty cycle < 2%

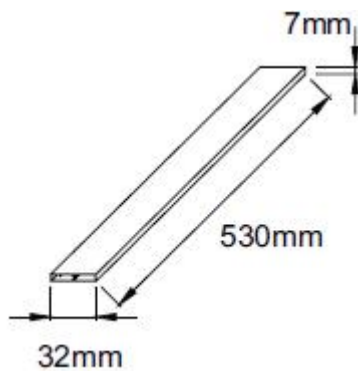
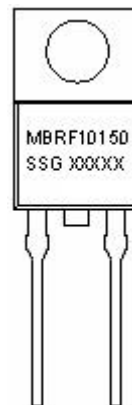
Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	T_J	-	-55 to +175	$^{\circ}\text{C}$
Storage Temperature	T_{stg}	-	-55 to +175	$^{\circ}\text{C}$
Typical Thermal Resistance Junction to Case	$R_{\theta\text{JC}}$	DC operation	3.5	$^{\circ}\text{C/W}$
Approximate Weight	wt	-	1.6	g
Case Style	ITO-220AC			

Ratings and Characteristics Curves
Typical Forward Characteristics

Typical Reverse Characteristics

Typical Junction Capacitance


Mechanical Dimensions ITO-220AC


SYMBOL	Millimeters		
	MIN.	TYP.	MAX.
A	4.30	4.50	4.70
A1	1.10	1.30	1.50
A2	2.80	3.00	3.20
A3	2.50	2.70	2.90
b	0.50	0.60	0.75
b1	1.10	1.20	1.35
b2	1.50	1.60	1.75
c	0.55	0.60	0.75
D	14.80	15.00	15.20
E	9.96	10.16	10.36
e	-	2.55	-
e1	-	5.10	-
H1	6.50	6.70	6.90
L	12.70	13.20	13.70
L1	1.60	1.80	2.00
L2	0.80	1.00	1.20
L3	0.60	0.80	1.00
L4	-	1.10	1.50
ΦP1(上□)	3.30	3.50	3.70
ΦP2(下□)	2.99	3.19	3.39
Q	2.50	2.70	2.90
Θ1		5°	
Θ2		4°	
Θ3		10°	
Θ4		5°	
Θ5		5°	

Tube Specification

Marking Diagram


Where XXXXX is YYWWL

- MBR = Device Type
- F = Package type
- 10 = Forward Current (10A)
- 150 = Reverse Voltage (150V)
- SSG = SSG
- YY = Year
- WW = Week
- L = Lot Number

Cautions: Molding resin
 Epoxy resin UL:94V-0

Ordering Information

Device	Package	Shipping
MBRF10150	ITO-220AC (Pb-Free)	50 pcs/ tube

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

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